RoHS

HALOGEN

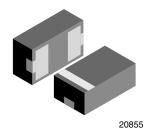
FREE

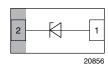
GREEN



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ESD Protection Diode in LLP1006-2L





MARKING (example only)



Bar = cathode marking

X = date code

Y = type code (see table below)

DESIGN SUPPORT TOOLS click logo to get started



FEATURES

- Ultra compact LLP1006-2L package
- Low package height < 0.4 mm
- 1-line ESD protection
- Low leakage current < 0.5 μA
- Low load capacitance C_D = 15 pF $(V_R = 2.5 V; f = 1 MHz)$
- ESD immunity acc. IEC 61000-4-2 ± 30 kV contact discharge
 - ± 30 kV air discharge
- High surge current acc. IEC 61000-4-5 I_{PP} > 3.5 A
- Soldering can be checked by standard vision inspection. No X-ray necessary
- Pin plating NiPdAu (e4) no whisker growth
- e4 precious metal (e.g. Ag, Au, NiPd, NiPdAu) (no Sn)
- PATENT(S): www.vishay.com/patents
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

ORDERING INFORMATION					
DEVICE NAME ORDERING CODE		TAPED UNITS PER REEL (8 mm TAPE on 7" REEL)	MINIMUM ORDER QUANTITY		
VESD03A1B-HD1	VESD03A1B-HD1-GS08	8000	8000		

PACKAGE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
VESD03A1B-HD1	LLP1006-2L	J	0.72 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

ABSOLUTE MAXIMUM RATINGS VESD03A1B-HD1						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5; t _P = 8/20 μs; single shot	I _{PPM}	3.5	Α		
Peak pulse power	Acc. IEC 61000-4-5; t _P = 8/20 μs; single shot	P_{PP}	31	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-40 to +125	°C		
Storage temperature		T _{stg}	-55 to +150	°C		

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and international patents.



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ELECTRICAL CHARACTERISTICS VESD03A1B-HD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	3.3	V	
Reverse voltage	At I _R = 0.5 μA	V_R	3.3	-	-	V	
Reverse current	At V _R = 3.5 V	I _R	-	0.04	0.5	μΑ	
Reverse breakdown voltage	At I _R = 1 mA	V_{BR}	5	6	6.6	V	
Reverse clamping voltage	At I _{PP} = 1 A	V _C	-	6.2	7.5	V	
	At I _{PP} = I _{PPM} = 3.5 A	V _C	-	7.6	9	V	
Forward clamping voltage	At I _{PP} = 0.2 A	V _F	-	0.9	1.2	V	
	At I _{PP} = 1 A	V _F	-	1.25	-	V	
	At I _{PP} = I _{PPM} = 3.5 A	V _F	-	1.8	-	V	
Capacitance	At $V_R = 0 V$; $f = 1 MHz$	C _D	-	25	28	pF	
	At V _R = 2.5 V; f = 1 MHz	C _D	-	15	-	pF	

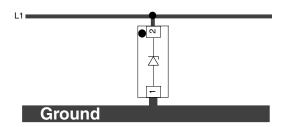
BIAs-MODE (bidirectional asymmetrical protection mode)

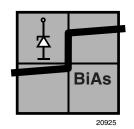
With the VESD03A1B-HD1 one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between data line and ground offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the VESD03A1B-HD1 clamping behavior is bidirectional and asymmetrical (BiAs).





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TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

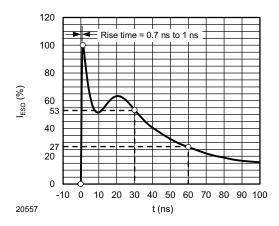


Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω /150 pF)

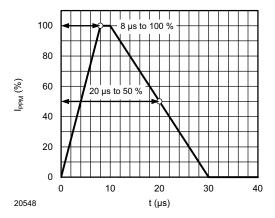


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form acc. IEC 61000-4-5

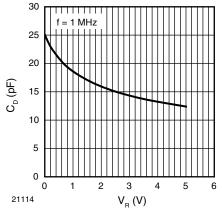


Fig. 3 - Typical Capacitance C_{D} vs. Reverse Voltage V_{R}

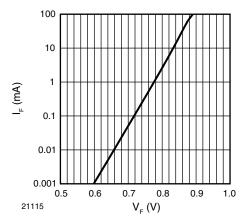


Fig. 4 - Typical Forward Current I_F vs. Forward Voltage V_F

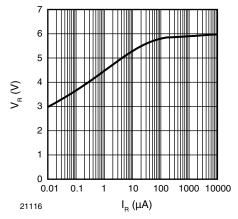


Fig. 5 - Typical Reverse Voltage V_R vs. Reverse Current I_R

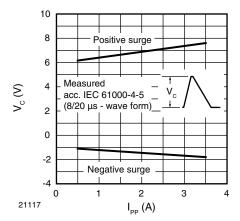


Fig. 6 - Typical Peak Clamping Voltage V_C vs. Peak Pulse Current I_{PP}



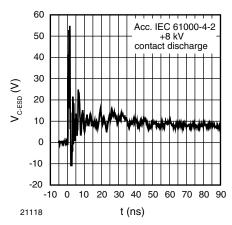


Fig. 7 - Typical Clamping Performance at + 8 kV Contact Discharge (acc. IEC 61000-4-2)

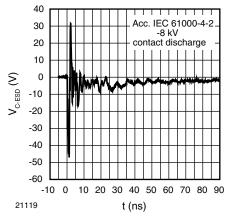


Fig. 8 - Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

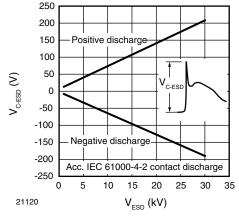
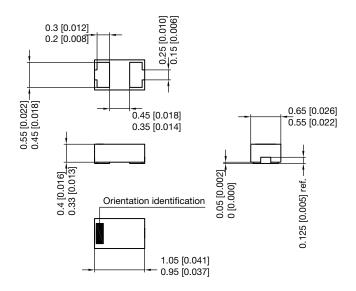


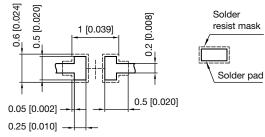
Fig. 9 - Typical Peak Clamping Voltage at ESD Contact Discharge (acc. IEC 61000-4-2)

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PACKAGE DIMENSIONS in millimeters (inches): LLP1006-2L

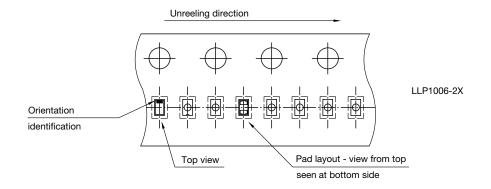


Foot print recommendation:



Pad Design Patented: (PUS 9.018.537 B2)

Document no.: S8-V-3906.04-005 (4) Rev. 7 - Date: 11.May 2016 20812



S8-V-3906.04-017 (4) 02.05.2017 22965



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